

**23 EDS Members Elected to the IEEE Grade of Fellow  
Effective 1 January 2006**

**Muhammad Alam, Purdue University, West Lafayette, IN, USA**  
*for contributions to complementary metal oxide semiconductors (CMOS)  
circuit reliability and computational models for electronics and  
optoelectronics*

**Jesus del Alamo, Massachusetts Institute of Technology, Cambridge,  
MA, USA**  
*for contributions to microelectronic devices*

**Seshu Desu, University of Massachusetts-Amherst, Amherst, MA, USA**  
*for contributions to development of ferroelectric thin film devices*

**Andreas Andreou, Johns Hopkins University, Baltimore, MD, USA**  
*for contributions to energy efficient sensory microsystems*

**Gary Bernstein, University of Notre Dame, Notre Dame, IN, USA**  
*for contributions to techniques for fabricating nanoscale devices and  
circuits*

**Steve Chung, National Chiao Tung University, Hsinchu, Taiwan**  
*for contributions to reliability in ultra-thin-oxide complementary metal oxide  
semiconductor (CMOS) devices*

**Simon Deleonibus, CEA LETI, Grenoble Cedex 9, France**  
*for contributions to nanoscaled complementary metal oxide semiconductor  
(CMOS) devices technology*

**Hector De Los Santos, NanoMEMS Research, LLC, Irvine, CA, USA**  
*for contributions to radio frequency (RF) and microwave micro electro-  
mechanical systems (MEMS) devices and applications*

**Martin Giles, Intel Corporation, Hillsboro, OR, USA**  
*for contributions to technology computer aided design (TCAD) modeling of  
processes and devices*

**Hideki Hayashi, Sumitomo Electric Industries, Tokyo, Japan**  
*for contributions to and leadership in compound semiconductor device  
technologies*

**Larry Hornbeck, Texas Instruments DLP Products, Van Alstyne, TX, USA**

*for invention, development, and applications of the Digital Micromirror Device*

**Qin (Alex) Huang, North Carolina State University, Raleigh, NC, USA**

*for contributions to emitter turn-off thyristor technology and its applications*

**Muhammad Khan, University of South Carolina, Columbia, SC, USA**

*for contributions to the development of III-nitride electronic sensor systems*

**Mong-Song Liang, TSMC (Taiwan Semiconductor Manufacturing Company, Ltd), Hsin Chu, Taiwan, ROC**

*for contributions to semiconductor manufacturing technologies*

**Gary May, Georgia Institute of Technology, Atlanta, GA, USA**

*for contributions to semiconductor manufacturing and engineering education*

**David Seiler, National Institute of Standards and Technology, Gaithersburg, MD, USA**

*for leadership in the development of critical metrology and measurement science at the micro and nano levels*

**Goran Stemme, Royal Institute of Technology, Stockholm, Sweden**

*for contributions to micro electro-mechanical systems (MEMS)*

**Yu-Chong Tai, California Institute of Technology, Pasadena, CA, USA**

*for contributions to integrated nano/micro electro-mechanical systems (MEMS) and nano/micro-fluidics for Lab-on-a-Chip applications*

**Katsuyoshi Washio, Central Research Laboratory, Hitachi, Ltd., Kokubunji, Tokyo, Japan**

*for contributions to high-speed silicon and silicon germanium bipolar/Bi complementary metal oxide semiconductors (CMOS) device and circuit technologies*

**Werner Weber, Infineon Technologies, Munich, Germany**

*for contributions to metal oxide semiconductors (MOS) device physics*

**Burnell West, Credence Systems Corporation, San Jose, CA, USA**

*for contributions to high-performance automatic test equipment*

**Gerald Witt, Air Force Office Scientific Research, Arlington, VA, USA**  
*for the promotion of research in compound semiconductor devices*

**Usha Varshney, National Science Foundation, Arlington, VA, USA**  
*for technical leadership in sensor technologies and systems*